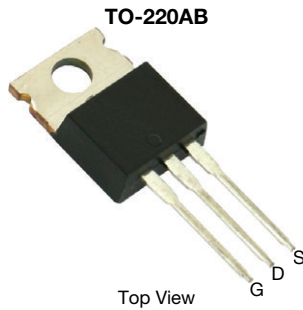


P-Channel 60 V (D-S) MOSFET



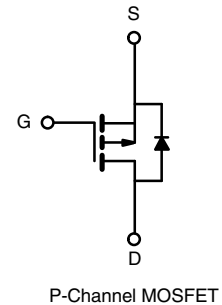
FEATURES

- TrenchFET® power MOSFET
- 100 % UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

APPLICATIONS

- Load switch



| PRODUCT SUMMARY | |
|---|--------|
| V_{DS} (V) | -60 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = -10$ V | 0.0195 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V | 0.0250 |
| Q_g typ. (nC) | 76 |
| I_D (A) ^a | -53 |
| Configuration | Single |

| ORDERING INFORMATION | |
|----------------------|----------------|
| Package | TO-220AB |
| Lead (Pb)-free | SUP53P06-20-E3 |

| ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted) | | | | |
|---|----------------|---------------|--------------------|----|
| PARAMETER | SYMBOL | LIMIT | UNIT | |
| Drain-source voltage | V_{DS} | -60 | V | |
| Gate-source voltage | V_{GS} | ± 20 | | |
| Continuous drain current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | -53 ^a | A |
| | | $T_C = 70$ °C | -46.8 | |
| | | $T_A = 25$ °C | 9.2 ^b | |
| | | $T_A = 70$ °C | -8.1 ^b | |
| Pulsed drain current | I_{DM} | -150 | | |
| Avalanche current pulse | $L = 0.1$ mH | I_{AS} | -45 | |
| Single pulse avalanche energy | | E_{AS} | 101 | mJ |
| Continuous source-drain diode current | | $T_C = 25$ °C | 69 ^a | A |
| | | $T_A = 25$ °C | 2.1 ^b | |
| Maximum power dissipation | P_D | $T_C = 25$ °C | 104.2 ^a | W |
| | | $T_C = 70$ °C | 66.7 ^a | |
| | | $T_A = 25$ °C | 3.1 ^b | |
| | | $T_A = 70$ °C | 2 ^b | |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|------------|---------|------|------|
| PARAMETER | SYMBOL | TYPICAL | MAXIMUM | UNIT | |
| Maximum junction-to-ambient ^b | Steady state | R_{thJA} | 33 | 40 | °C/W |
| Maximum junction-to-case | | | | | |

Notes

a. Based on $T_C = 25$ °C



b. Surface mounted on 1" x 1" FR4 board

| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|---|--------------------------------------|--|------|--------|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-source breakdown voltage | V _{DS} | V _{GS} = 0 V, I _D = -250 μA | -60 | - | - | V |
| V _{DS} temperature coefficient | ΔV _{DS} /T _J | I _D = -250 μA | - | 68 | - | mV/°C |
| V _{GS(th)} temperature coefficient | ΔV _{GS(th)} /T _J | | - | -5.2 | - | |
| Gate-source threshold voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = -250 μA | -1 | - | -3 | V |
| Gate-source leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | - | - | ± 100 | nA |
| Zero gate voltage drain current | I _{DSS} | V _{DS} = -60 V, V _{GS} = 0 V | - | - | -1 | μA |
| | | V _{DS} = -60 V, V _{GS} = 0 V, T _J = 55 °C | - | - | -10 | |
| On-state drain current ^a | I _{D(on)} | V _{DS} = -5 V, V _{GS} = -10 V | -120 | - | - | A |
| Drain-source on-state resistance ^a | R _{DS(on)} | V _{GS} = -10 V, I _D = -30 A | - | 0.0160 | 0.0195 | Ω |
| | | V _{GS} = -4.5 V, I _D = -20 A | - | 0.0200 | 0.0250 | |
| Forward transconductance ^a | g _{fs} | V _{DS} = -15 V, I _D = -50 A | 20 | - | - | S |
| Dynamic ^b | | | | | | |
| Input capacitance | C _{iss} | V _{DS} = -25 V, V _{GS} = 0 V, f = 1 MHz | - | 3500 | - | pF |
| Output capacitance | C _{oss} | | - | 390 | - | |
| Reverse transfer capacitance | C _{rss} | | - | 290 | - | |
| Total gate charge | Q _g | V _{DS} = -30 V, V _{GS} = -10 V, I _D = -55 A | - | 76 | 115 | nC |
| | | V _{DS} = -30 V, V _{GS} = -4.5 V, I _D = -55 A | - | 38 | 60 | |
| Gate-source charge | Q _{gs} | | - | 16 | - | |
| Gate-drain charge | Q _{gd} | | - | 19 | - | |
| Gate resistance | R _g | f = 1 MHz | - | 5.2 | - | Ω |
| Turn-on delay time | t _{d(on)} | V _{DD} = -2 V, R _L = 2 Ω I _D ≅ -10 A, V _{GEN} = -10 V, R _g = 1 Ω | - | 10 | 15 | ns |
| Rise time | t _r | | - | 7 | 15 | |
| Turn-off delay time | t _{d(off)} | | - | 70 | 110 | |
| Fall time | t _f | | - | 40 | 60 | |
| | | | | | | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous source-drain diode current | I _S | T _C = 25 °C | - | - | -69 | A |
| Pulse diode forward current ^a | I _{SM} | | - | - | -150 | |
| Body diode voltage | V _{SD} | I _S = -30 A | - | -1 | -1.5 | V |
| Body diode reverse recovery time | t _{rr} | I _F = -50 A, di/dt = 100 A/μs, T _J = 25 °C | - | 45 | 68 | ns |
| Body diode reverse recovery charge | Q _{rr} | | - | 59 | 120 | nC |
| Reverse recovery fall time | t _a | | - | 29 | - | ns |
| Reverse recovery rise time | t _b | | - | 16 | - | |

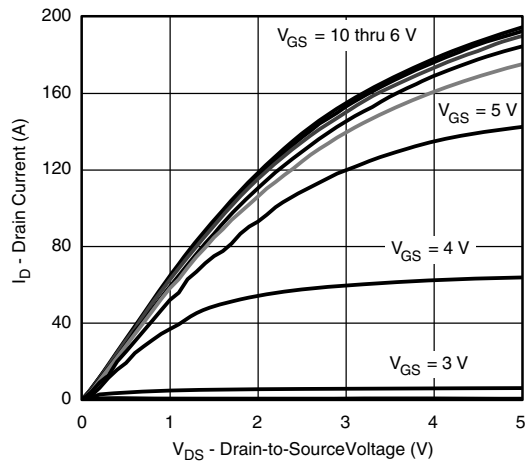
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing

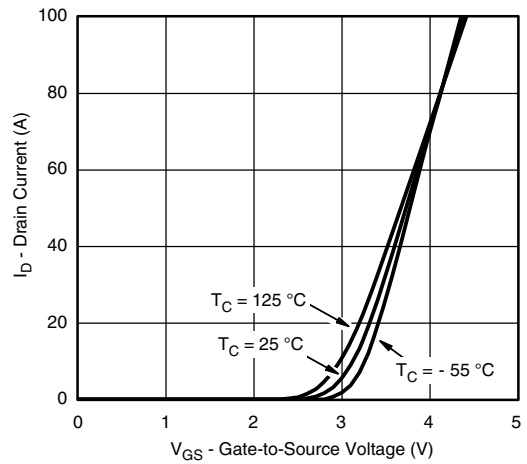
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



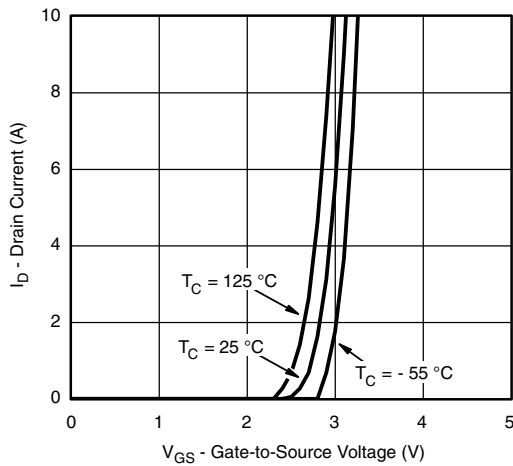
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



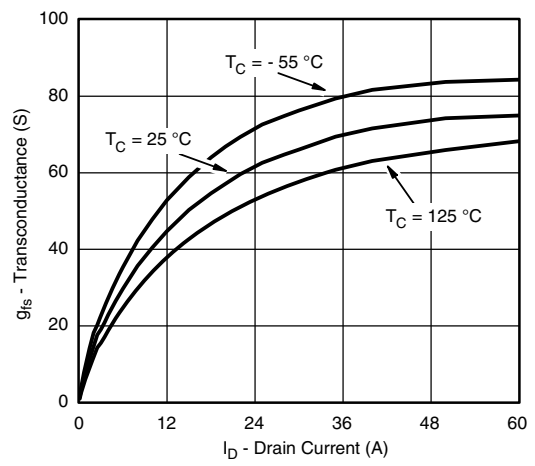
Output Characteristics



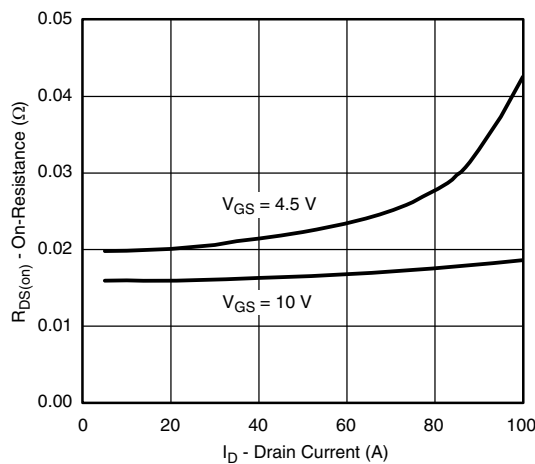
Transfer Characteristics



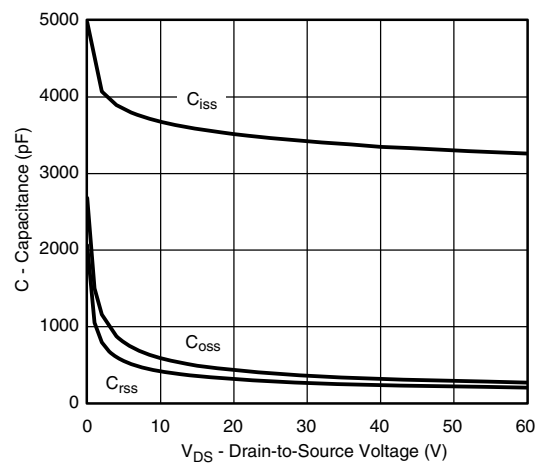
Transfer Characteristics



Transconductance



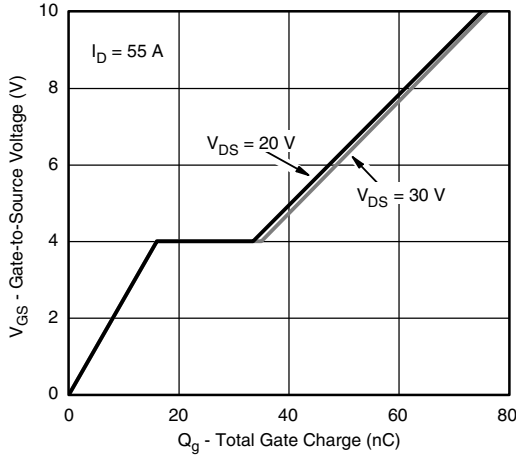
On-Resistance vs. Drain Current



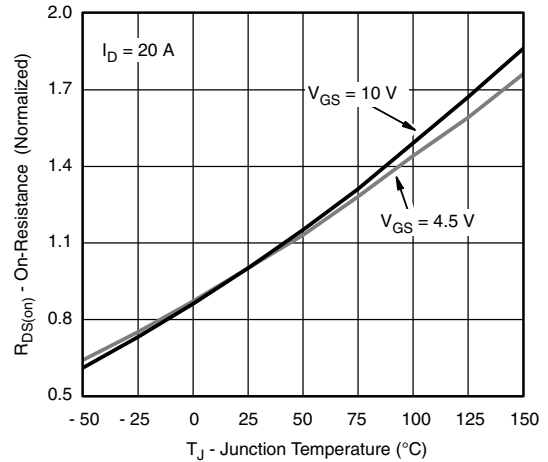
Capacitance



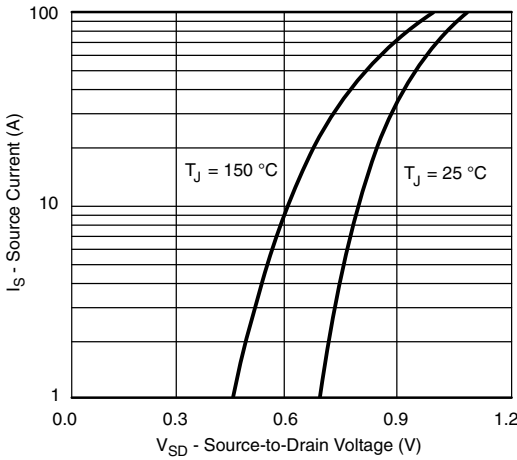
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



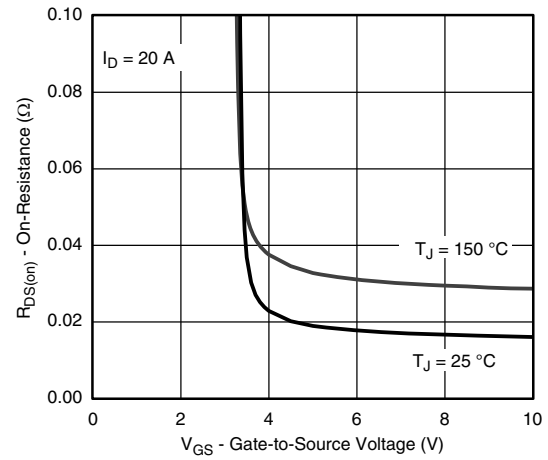
Gate Charge



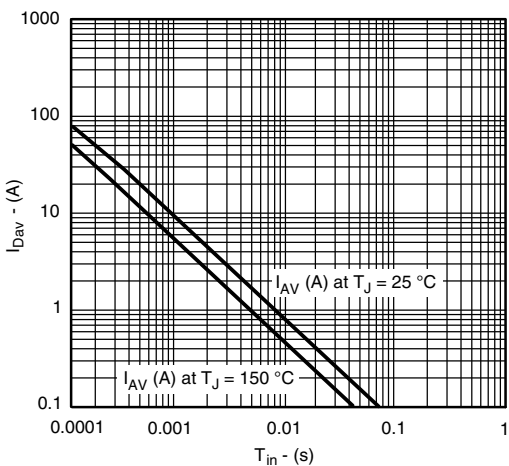
On-Resistance vs. Gate-to-Source Voltage



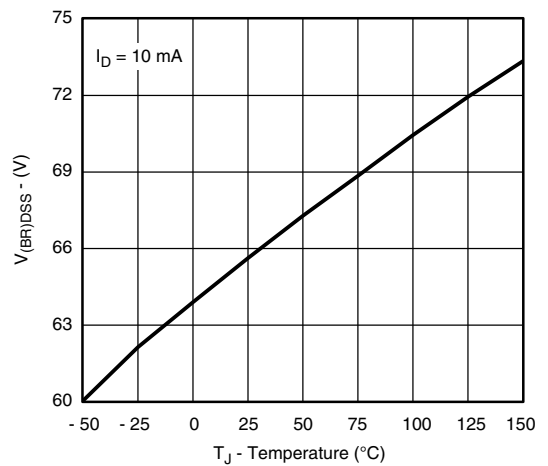
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



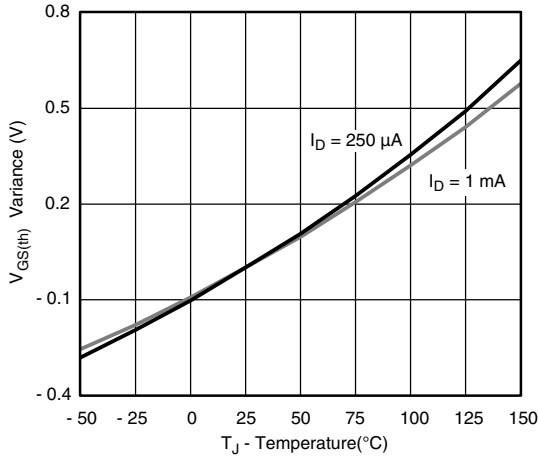
Single Pulse Avalanche Current Capability vs. Time



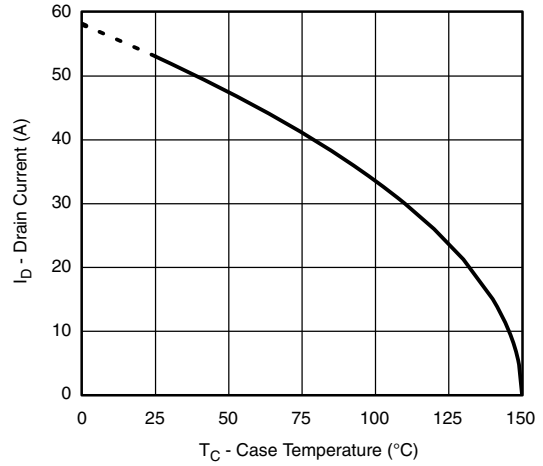
Drain-Source Breakdown Voltage vs. Junction Temperature



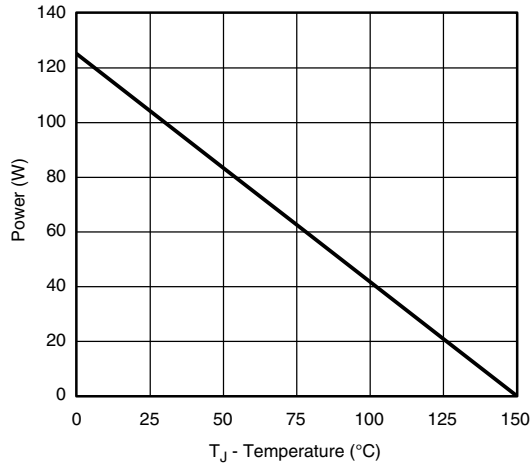
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



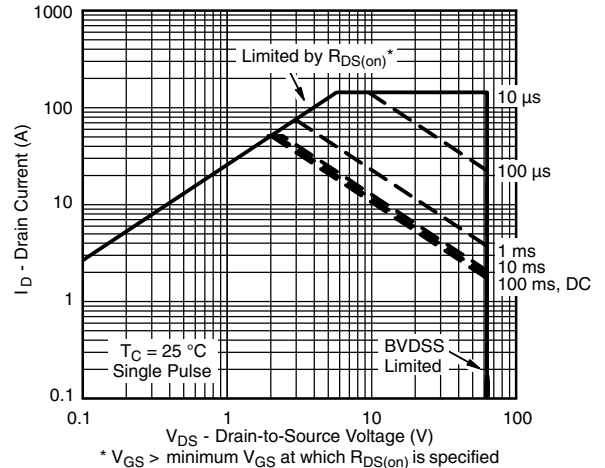
Threshold Voltage



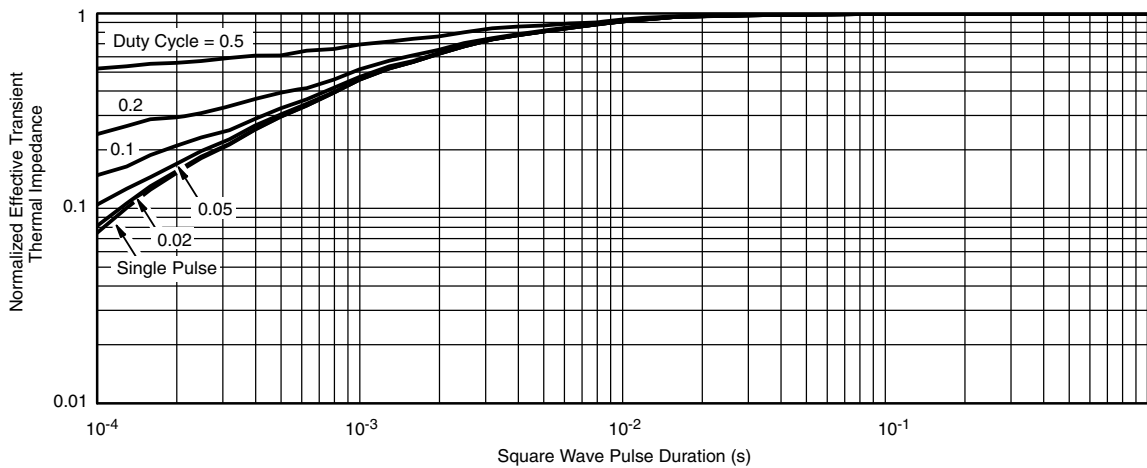
Max. Drain Current vs. Case Temperature



Power Derating, Junction-to-Case



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-220AB

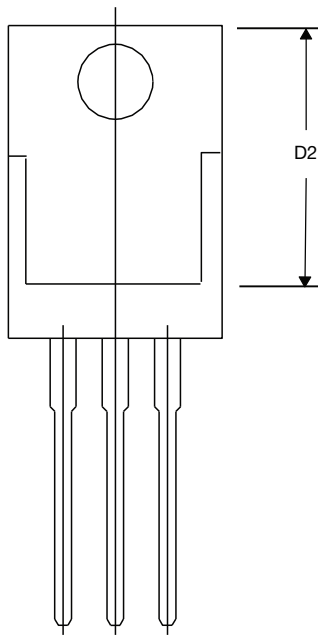


| DIM. | MILLIMETERS | | INCHES | |
|-----------------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.25 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.01 | 0.027 | 0.040 |
| b(1) | 1.20 | 1.73 | 0.047 | 0.068 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.85 | 15.49 | 0.585 | 0.610 |
| D2 | 12.19 | 12.70 | 0.480 | 0.500 |
| E | 10.04 | 10.51 | 0.395 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.09 | 6.48 | 0.240 | 0.255 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.35 | 14.02 | 0.526 | 0.552 |
| L(1) | 3.32 | 3.82 | 0.131 | 0.150 |
| $\varnothing P$ | 3.54 | 3.94 | 0.139 | 0.155 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

ECN: T14-0413-Rev. P, 16-Jun-14
DWG: 5471

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM





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